

TECHNICAL DATA, PROVISIONAL DATA ONLY  
DATA SHEET 4984, REV. B

## HERMETIC SILICON CARBIDE RECTIFIER

**DESCRIPTION:** A 1200-VOLT, 40 AMP POWER SILICON CARBIDE RECTIFIER IN A HERMETIC TO-258 PACKAGE WITH CERAMIC SEAL

### FEATURES:

- NO RECOVERY TIME OR REVERSE RECOVERY LOSSES
- NO TEMPERATURE INFLUENCE ON SWITCHING BEHAVIOR
- SCREENED VERSIONS ARE AVAILABLE

### MAXIMUM RATINGS

ALL RATINGS ARE @  $T_C = 25^\circ\text{C}$  UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MAX.	UNITS
PEAK INVERSE VOLTAGE	PIV	1200	Volts
MAXIMUM DC OUTPUT CURRENT PER LEG (With Cathode Maintained @ $T_C = 65^\circ\text{C}$ )	$I_O$	20	Amps
MAXIMUM REPETITIVE FORWARD SURGE CURRENT PER LEG ( $t = 8.3\text{ms}$ , Sine) $T_C = 25^\circ\text{C}$	$I_{FRM}$	60	Amps
MAXIMUM NON-REPETITIVE FORWARD SURGE CURREN PER LEG ( $t = 10\mu\text{s}$ , pulse) $T_C = 25^\circ\text{C}$	$I_{FSM}$	250	Amps
MAXIMUM POWER DISSIPATION, $T_C = 25^\circ\text{C}$	$P_d$	80	W
MAXIMUM THERMAL RESISTANCE, Junction to Case, Per Dual Package	$R_{\theta JC}$	0.5	$^\circ\text{C/W}$
MAXIMUM OPERATING TEMPERATURE RANGE	Top	-55 to +175	$^\circ\text{C}$
MAXIMUM STORAGE TEMPERATURE RANGE*	Tstg	-55 to +200	$^\circ\text{C}$

\* Note: SiC semiconductors will handle at or above this operating and storage temperature. However, extended operational use of the packaged device above 175C may reduce its future performance. All qualification testing and screening per MIL-PRF-19500 will only be performed to 175C.

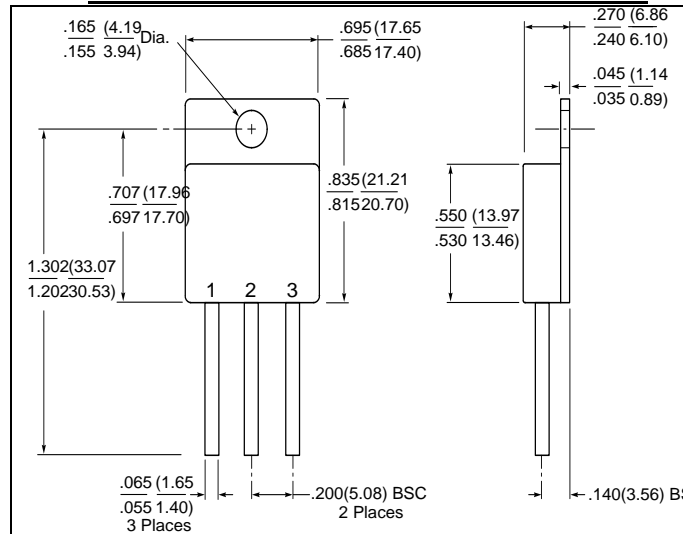
### ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	TYP	MAX.	UNITS
FORWARD VOLTAGE DROP PER LEG( $I_f = 20\text{A}$ ) $V_f$	$T_J = 25^\circ\text{C}$ $T_J = 175^\circ\text{C}$	1.6 2.5	1.8 3.0 Volts
REVERSE CURRENT PER LEG (1200V PIV) $I_r$	$T_J = 25^\circ\text{C}$ $T_J = 175^\circ\text{C}$	0.02 0.04	0.40 2.00 mA
JUNCTION CAPACITANCE ( $V_f = 400\text{V}$ , $f = 1\text{MHz}$ ) $C_T$ PER LEG	$T_J = 25^\circ\text{C}$	140	N/A pF
TOTAL CAPACITIVE CHARGE PER LEG ( $V_R = 1200\text{V}$ $I_F = 10\text{A}$ $di/dt = 500\text{A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$ ) $Q_C$		100	N/A nC

SENSITRON

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**MECHANICAL DIMENSIONS: IN Inches / mm**

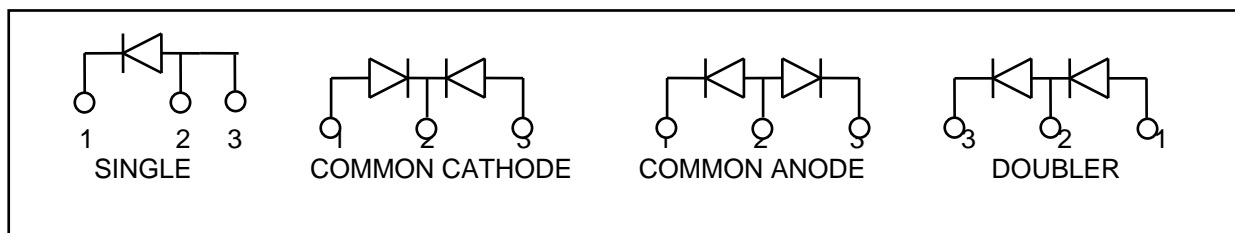


**TO-258**

**PINOUT TABLE**

TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE
DUAL RECTIFIER/COMMON CATHODE (P)	ANODE 1	COMMON CATHODE	ANODE 2
DUAL RECTIFIER/COMMON ANODE (N)	CATHODE 1	COMMON ANODE	CATHODE 2
DUAL RECTIFIER/DOUBLER (D)	ANODE	ANODE/ CATHODE	CATHODE

**SCHEMATIC**



## TYPICAL PERFORMANCE PER LEG

Figure 1. Forward Characteristics

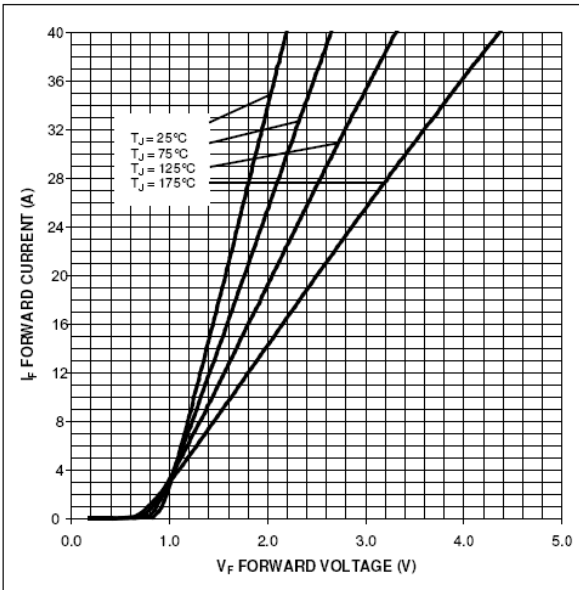
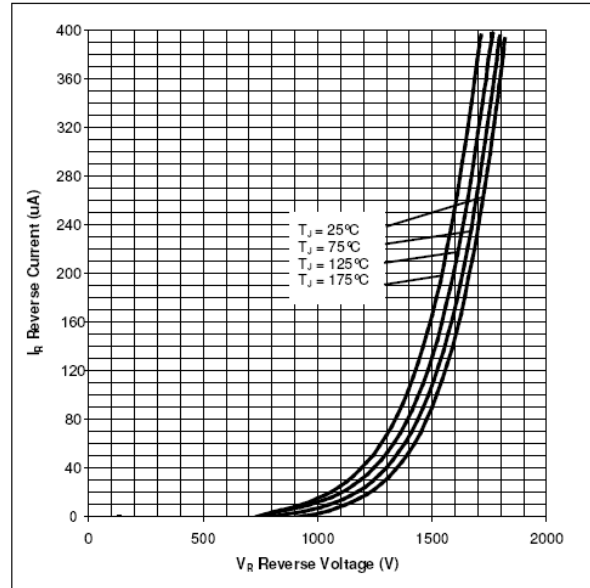


Figure 2. Reverse Characteristics



Application Note: Customers should be aware that at the current stage of technical development of SiC, the reverse avalanche capabilities of the device are limited.

Customer designs will need to accommodate these limitations and avoid exposure of the device to this and other potentially damaging conditions in their applications.

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